

# FDME410NZT

## N-Channel PowerTrench® MOSFET

20 V, 7 A, 26 mΩ

### Features

- Max  $r_{DS(on)}$  = 26 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 7$  A
- Max  $r_{DS(on)}$  = 31 mΩ at  $V_{GS} = 2.5$  V,  $I_D = 6$  A
- Max  $r_{DS(on)}$  = 39 mΩ at  $V_{GS} = 1.8$  V,  $I_D = 5$  A
- Max  $r_{DS(on)}$  = 53 mΩ at  $V_{GS} = 1.5$  V,  $I_D = 4$  A
- Low profile: 0.55 mm maximum in the new package MicroFET 1.6x1.6 **Thin**
- Free from halogenated compounds and antimony oxides
- HBM ESD protection level > 1800V (Note3)
- RoHS Compliant

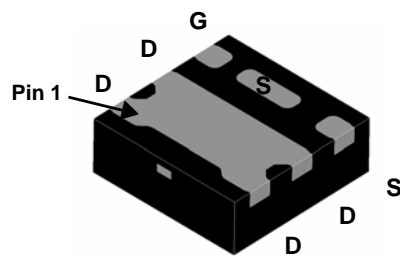


### General Description

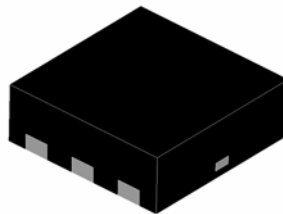
This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the  $r_{DS(ON)}$  @  $V_{GS} = 1.5$  V on special MicroFET leadframe.

### Applications

- Li-Ion Battery Pack
- Baseband Switch
- Load Switch
- DC-DC Conversion

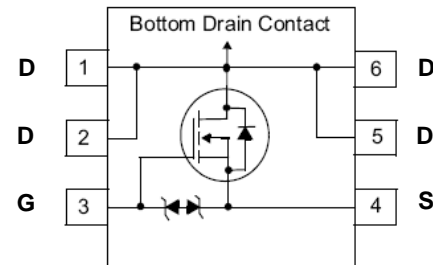


BOTTOM



TOP

MicroFET 1.6x1.6 Thin



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated Value	Units
$V_{DS}$	Drain to Source Voltage	20	V
$V_{GS}$	Gate to Source Voltage	±8	V
$I_D$	Drain Current -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	7	A
	-Pulsed	15	
$P_D$	Power Dissipation for Single Operation $T_A = 25^\circ\text{C}$ (Note 1a)	2.1	W
	Power Dissipation for Single Operation $T_A = 25^\circ\text{C}$ (Note 1b)	0.7	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	60	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	175	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
6T	FDME410NZT	MicroFET 1.6x1.6 <b>Thin</b>	7"	8 mm	5000 units

**Electrical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		18		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{ V}, V_{DS} = 0\text{ V}$			$\pm 10$	$\mu\text{A}$

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	0.4	0.7	1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-3		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$		19	26	m $\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 6\text{ A}$		20	31	
		$V_{GS} = 1.8\text{ V}, I_D = 5\text{ A}$		24	39	
		$V_{GS} = 1.5\text{ V}, I_D = 4\text{ A}$		31	53	
		$V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}, T_J = 125\text{ }^\circ\text{C}$		24	36	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 7\text{ A}$		35		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		770	1025	pF
$C_{oss}$	Output Capacitance			115	155	pF
$C_{rss}$	Reverse Transfer Capacitance			75	115	pF
$R_g$	Gate Resistance			1.9		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{ V}, I_D = 7\text{ A}, V_{GS} = 4.5\text{ V}, R_{GEN} = 6\text{ }\Omega$		7.3	15	ns
$t_r$	Rise Time			3.4	10	ns
$t_{d(off)}$	Turn-Off Delay Time			27	43	ns
$t_f$	Fall Time			3.2	10	ns
$Q_g$	Total Gate Charge		$V_{DD} = 10\text{ V}, I_D = 7\text{ A}, V_{GS} = 4.5\text{ V}$		9.2	13
$Q_{gs}$	Gate to Source Gate Charge			1.1		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			1.6		nC

**Drain-Source Diode Characteristics**

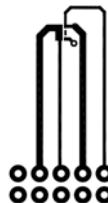
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.6\text{ A}$ (Note 2)		0.7	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		15	27	ns
$Q_{rr}$	Reverse Recovery Charge			3.5	10	nC

**Notes:**

- $R_{\theta JA}$  is determined with the device mounted on a  $1\text{ in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{ in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $60\text{ }^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper.

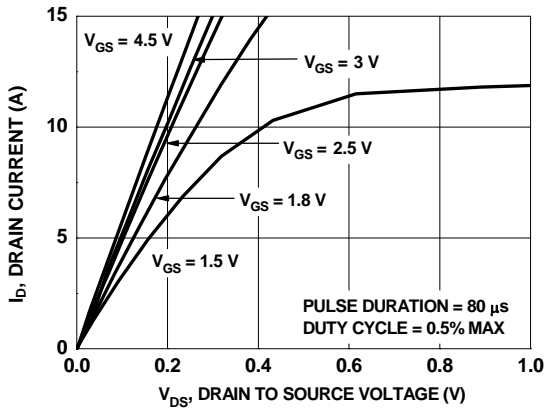


b.  $175\text{ }^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper.

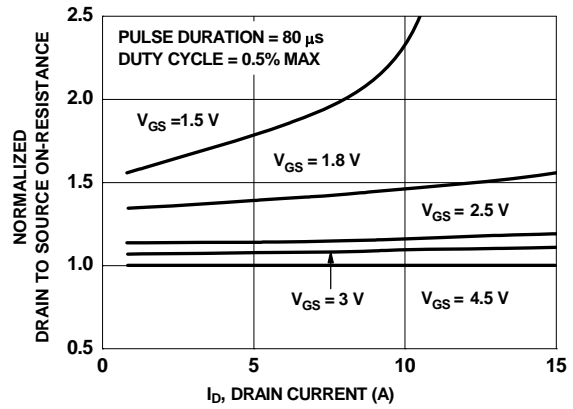
- Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

- The diode connected between the gate and source serves only as protection ESD. No gate overvoltage rating is implied.

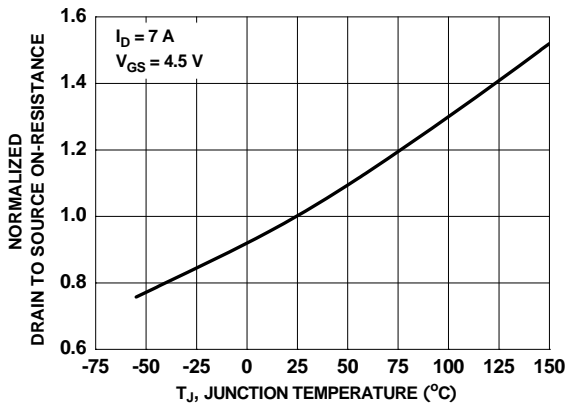
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



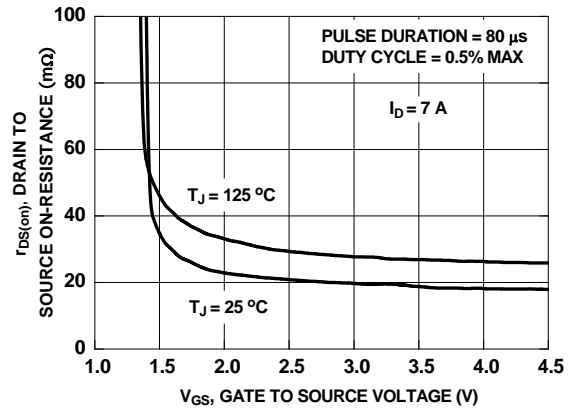
**Figure 1. On-Region Characteristics**



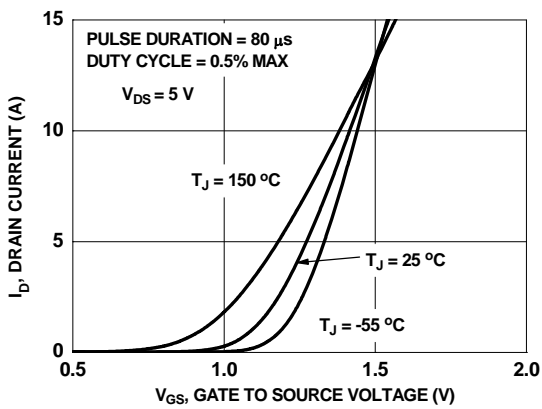
**Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage**



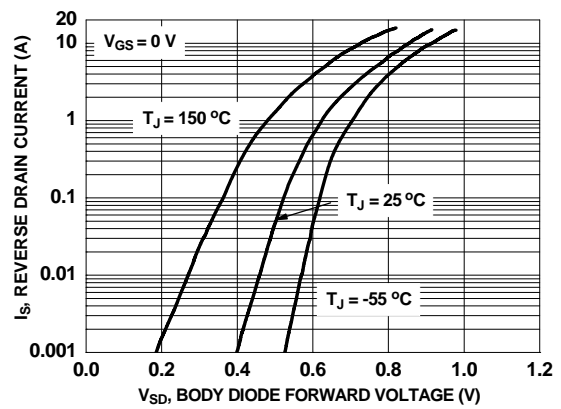
**Figure 3. Normalized On-Resistance vs Junction Temperature**



**Figure 4. On-Resistance vs Gate to Source Voltage**

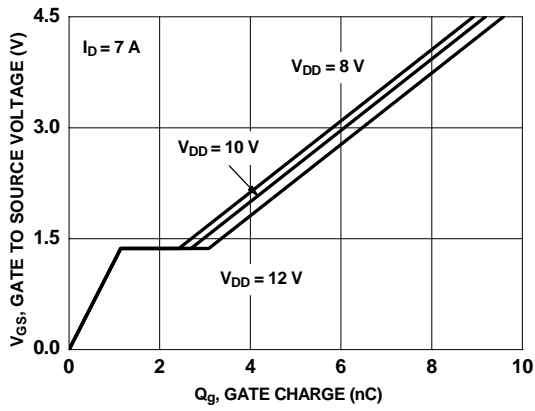


**Figure 5. Transfer Characteristics**

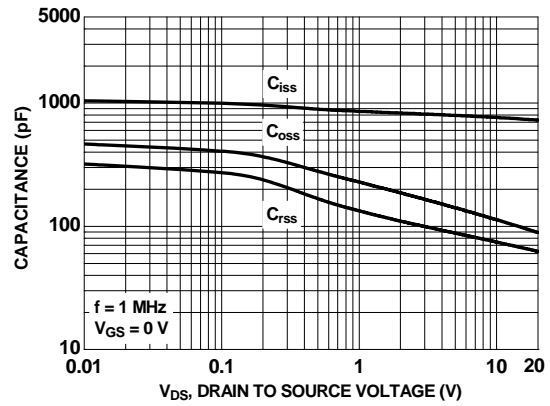


**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

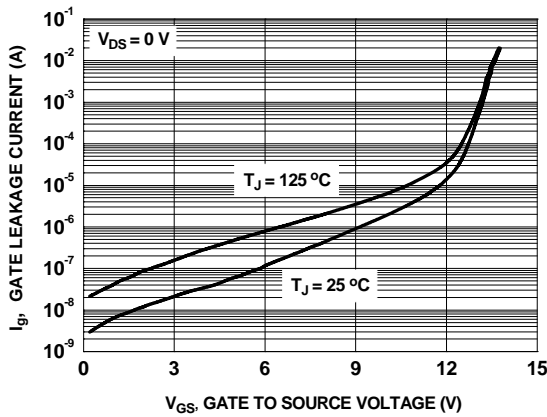
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



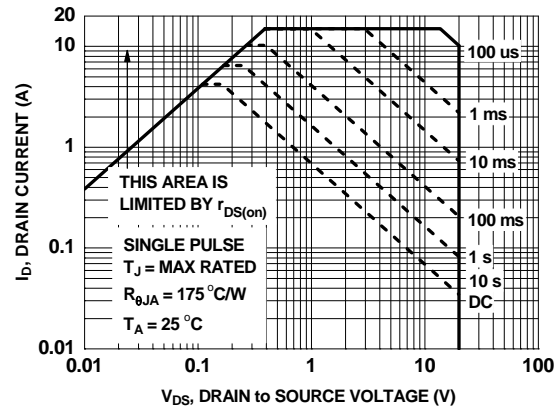
**Figure 7. Gate Charge Characteristics**



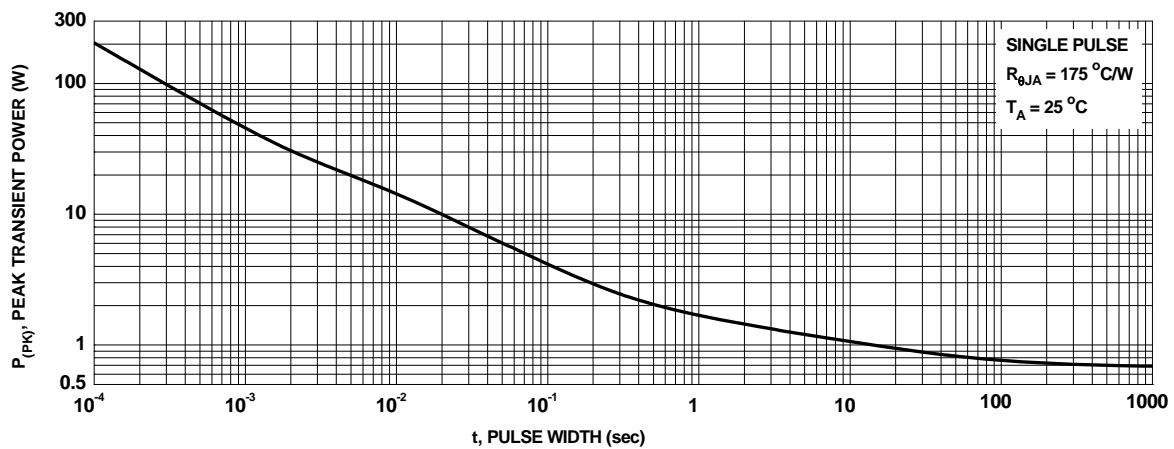
**Figure 8. Capacitance vs Drain to Source Voltage**



**Figure 9. Gate Leakage Current vs Gate to Source Voltage**

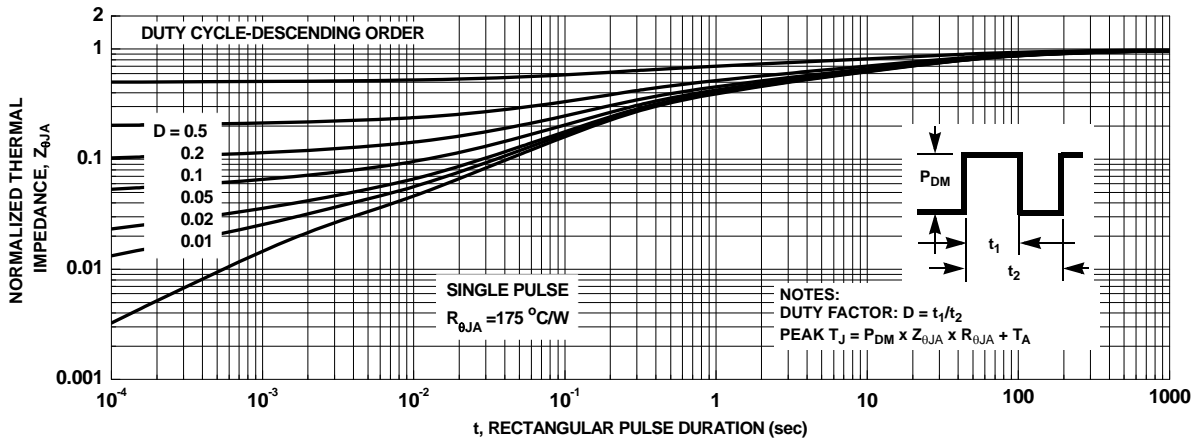


**Figure 10. Forward Bias Safe Operating Area**



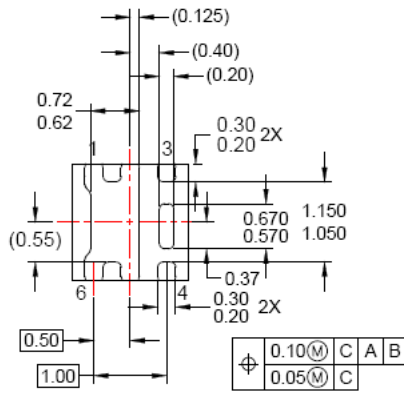
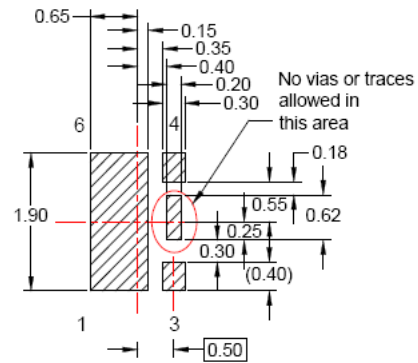
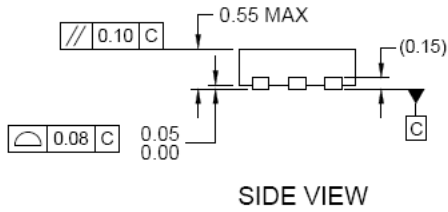
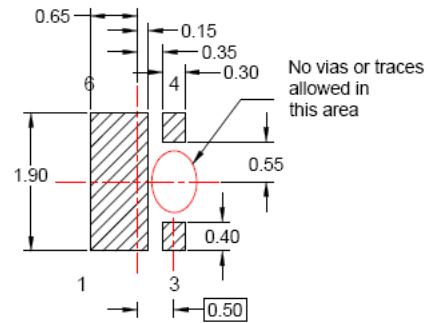
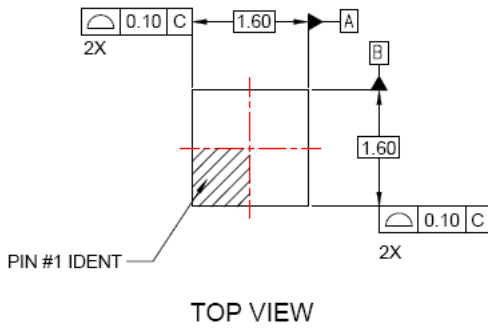
**Figure 11. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



**Figure 12. Junction-to-Ambient Transient Thermal Response Curve**

## Dimensional Outline and Pad Layout






- NOTES:
- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION
  - B. DIMENSIONS ARE IN MILLIMETERS.
  - C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  - D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY



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